INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)	Application Number
SETI-0001	09/966563
Applicant(s)	
Khan et al.	
Filing Date	**Group Art Unit**
September 27, 2001	2814

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

FB		"The Influence of the Strain-Induced Electric Field on the Charge Distribution in GaN-AlN-GaN Structure," A. D. Bykhovski et al., Journal of Applied Physics, Vol. 74, No. 11, December 1, 1993, pp.6734-6739.
FC		"Pyroelectricity in Gallium Nitride Thin Films," A. D. Bykhovski et al., Applied Physics Letters, Vol. 69, No. 21, November 18, 1996, pp. 3254-3256.

EXAMINER	DATE CONSIDERED
[signature] FRANK BROOKS	03/09/05

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	Applicant(s) Khan et al.	
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*EXAMINER INITIAL		OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*
PR		"Pyroelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.
		"Piezoeffect and Gate Current in AlGaN/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675.
		"Two-Dimensional Electron-Gas Density in AlxGa1-xN/GaN Heterostructure Field-Effect Transistors," N. Maeda et al., Applied Physics Letters, Vol. 73, No. 13, September 28, 1998, pp. 1856-1858.
		"Piezoelectric Charge Densities in AlGaN/GaN HFETs," P.M. Asbeck et al., Electronic Letters, Vol. 33, No. 14, July 3, 1997, 1230-1231.
		"Spontaneous Polarization and Piezoelectric Constants of III-V Nitrides," F. Bernardini et al., Physical Review B, Vol. 56, No. 16, October 15, 1997, pp. R10024-R10027.
		"Piezoelectric Doping and Elastic Strain Relaxation in AlGaN-GaN Heterostructure Field Effect Transistors," A. D. Bykhovski et al., Applied Physics Letters, Vol. 73, No. 24, December 14, 1998, pp. 3577-3579.
		"Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version).
		"Lattice and Energy Band Engineering in AlInGaN/GaN Heterostructures," M. A. Khan et al., Applied Physics Letters, Vol. 76, No. 9, February 28, 2000, pp. 1161-1163.
		"Electron Mobility in Modulation-Doped AlGaN-GaN Heterostructures," R. Gaska et al., Applied Physics Letters, Vol. 74, No. 2, January 11, 1999, pp. 287-289.
		"High Pinch-off Voltage AlGaN-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, Charlottesville, VA, December 1997, pp. 377-380.
		"Optoelectronic GaN-Based Field Effect Transistors," M. S. Shur et al., SPIE Vol. 2397, pp. 294-303.
		"Current/Voltage Characteristic Collapse in AlGaN/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2175-2176.

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[signature] ROLAND GRIFFIN	03/09/05

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